
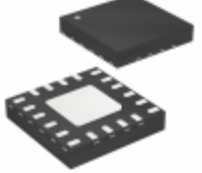




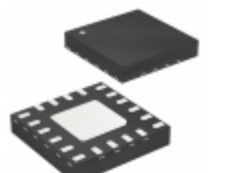


	<h2>SI3499DV-T1-E3</h2>
	<p>Hersteller-Teilenummer: SI3499DV-T1-E3</p> <hr/> <p>Hersteller / Marke: Vishay / Siliconix</p> <hr/> <p>Teil der Beschreibung: MOSFET P-CH 8V 5.3A 6-TSOP</p> <hr/> <p>Datenblätter:  SI3499DV-T1-E3.pdf</p> <hr/> <p>RoHs Status: Bleifrei / RoHS-konform</p> <hr/> <p>Lagerzustand: New original, 21825 pcs Stock Available.</p> <hr/> <p>Liefern von: Hong Kong</p> <hr/> <p>Versandweg: DHL/Fedex/TNT/UPS/EMS</p>
<p>Image may be representation. See specs for product details.</p>	

Spezifikationen

Teilenummer	SI3499DV-T1-E3
Hersteller	Vishay / Siliconix
Beschreibung	MOSFET P-CH 8V 5.3A 6-TSOP
Kategorie	Diskrete Halbleiterprodukte > Transistoren-FETs,
Teilstatus	21825 pcs Stock
Serie	TrenchFET®
Technologie	MOSFET (Metal Oxide)
Betriebstemperatur	-55°C ~ 150°C (TJ)
Befestigungsart	Surface Mount
Verpackung / Gehäuse	SOT-23-6 Thin, TSOT-23-6
Supplier Device-Gehäuse	6-TSOP
Verlustleistung (max)	1.1W (Ta)
Typ FET	P-Channel
FET-Merkmal	-
Drain-Source-Spannung (Vdss)	8V
Strom - Ununterbrochener Abfluss (Id) bei 25 ° C	5.3A (Ta)
Rds On (Max) @ Id, Vgs	23 mOhm @ 7A, 4.5V
VGS (th) (Max) @ Id	750mV @ 250µA
Gate Charge (Qg) (Max) @ Vgs	42nC @ 4.5V
Eingabekapazität (Ciss) (Max) @ Vds	-
Verpackung	Tape & Reel (TR)


























SI3499DV-T1-E3 ist neu im Original, Suche SI3499DV-T1-E3 Datenblätter, PDF, Inventar bei Y-IC.com Online, Bestellen Sie SI3499DV-T1-E3 Vishay / Siliconix mit Garantie und Vertrauen. Anfrage SI3499DV-T1-E3: Info@Y-IC.com

Sie können auch interessiert sein:

 <p>SI3500-A-GM Energy Micro (Silicon Labs) IC REG BUCK ADJ 0.4A 20QFN</p>	 <p>SI3499DV-T1-E3 Electro-Films (EFI) / Vishay MOSFET P-CH 8V 5.3A 6-TSOP</p>	 <p>SI3522V SANKEN SI3522V SANKEN</p>	 <p>SI3495DV-T1-GE3 Electro-Films (EFI) / Vishay MOSFET P-CH 20V 5.3A 6-TSOP</p>
 <p>SI3495DV-T1-GE3 Vishay / Siliconix MOSFET P-CH 20V 5.3A 6-TSOP</p>	 <p>SI3500-A-GMR Energy Micro (Silicon Labs) IC REG BUCK ADJ 0.4A 20QFN</p>	 <p>SI3499DV-T1-GE3 Vishay / Siliconix MOSFET P-CH 8V 5.3A 6-TSOP</p>	 <p>SI3495DV-T1-E3 Electro-Films (EFI) / Vishay MOSFET P-CH 20V 5.3A 6-TSOP</p>

heiße Teile

Mehr

 SI3483CDV-T1-GE3	 SI3483CDV-T1-GE3	 SI3483DV-T1-E3	 SI3483DV-T1-E3	 SI3483DV-T1-GE3
 SI3483DV-T1-GE3	 SI3493BDV-T1-E3	 SI3493BDV-T1-E3	 SI3493BDV-T1-E3-S	 SI3493BDV-T1-GE3
 SI3493BDV-T1-GE3	 SI3493DDV-T1-GE3	 SI3493DDV-T1-GE3	 SI3493DV	 SI3493DV-T1
 SI3493DV-T1-E3	 SI3493DV-T1-E3	 SI3493DV-T1-E3	 SI3493DV-T1-GE3	 SI3493DV-T1-GE3
 SI3495DV	 SI3495DV-T1-E3	 SI3495DV-T1-E3	 SI3495DV-T1-GE3	 SI3495DV-T1-GE3
 SI3499DV-T1-E3	 SI3499DV-T1-GE3	 SI3499DV-T1-GE3	 SI3500-A-GM	 SI3529DV-T1-GE3
 SI3529DV-T1-GE3	 SI3552DV	 SI3552DV-T1	 SI3552DV-T1-E3	 SI3552DV-T1-E3
 SI3552DV-T1-GE3	 SI3552DV-T1-GE3	 SI3585CDV	 SI3585CDV-T1-GE3	 SI3585CDV-T1-GE3
 SI3585DV	 SI3585DV-T1	 SI3585DV-T1-E3	 SI3585DV-T1-E3	 SI3585DV-T1-GE3
 SI3585DV-T1-GE3	 SI3586DS-TI-E3	 SI3586DV	 SI3586DV-T1-E3	 SI3586DV-T1-E3

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